



On December 5, 2005 at the Plenary session of the IEEE EDS International Electron Devices Meeting (IEDM) in Washington, D.C., the 2005 EDS President, Hiroshi Iwai, presented a number of 2005 IEEE/EDS Fellows with certificates to congratulate them on being elected IEEE Fellows. Fourteen of the 40 EDS members elected to the IEEE grade of Fellow for 2005 attended the presentation.

**40 EDS Members Elected to the IEEE Grade of Fellow
Effective 1 January 2005**

**Supriyo Bandyopadhyay, Virginia Commonwealth Univ., Richmond, VA,
USA**

for contributions to device applications of nanostructures

**Henri Marius Baudrand, Ecole Nationale Supérieure
d'Electrotechnique, Toulouse, France**

*for contributions to the electromagnetic modeling of microwave circuits and
antennas*

Robert Christopher Baumann, Texas Instruments, Dallas, Texas, USA

*for contributions to the understanding of the reliability impact of terrestrial
radiation mechanisms in commercial electronics*

Duane S. Boning, MIT, Cambridge, MA, USA
for contributions to modeling and control in semiconductor manufacturing

William D. Brown, University of Arkansas, Fayetteville, AR, USA
for leadership in furthering education of high density electronics

Jeff D. Bude, Agere Systems, New Providence, NJ, USA
for contributions to the deep submicron MOSFETs

Robert S. Chau, Intel Corporation, Beaverton, OR, USA
for contributions to gate dielectric and transistor technology for microprocessors

Clifton G. Fonstad, Massachusetts Inst. of Technology, Cambridge, MA, USA
for leadership in compound semiconductor heterostructure devices

William Robert Frensley, University of Texas at Dallas, Richardson, TX, USA
for contributions to nanometer-scale quantum semiconductor devices

Guido V. Groeseneken, IMEC, Leuven, Belgium
for his contributions to the physical understanding and the modeling of reliability of metal oxide semiconductor field effect transistors

Ken-ya Hashimoto, Chiba University, Chiba, Japan
for contributions to simulation and design for surface acoustic wave devices

George L Heiter, Heiter Microwave Consulting, Westford, MA, USA
for contributions to microwave circuits, including linear amplifiers and space diversity combiners

G. Benjamin Hocker, Honeywell Laboratories (Retired), Minnetonka, MN, USA
for leadership in microelectromechanical system technology

James Albert Hutchby, Semiconductor Research Corp., Triangle Park, NC, USA
for contributions to the design of low power static random access memories

Tadao Ishibashi, NTT Electronics Corporation, Kanagawa, Japan
for contributions to high-speed and optoelectronic semiconductor devices

Noble M. Johnson, Palo Alto Research Center, Palo Alto, CA, USA
for contributions to the control of impurities in semiconductors

Masaaki Kuzuhara, NEC Corporation, Otsu, Shiga Prefecture, Japan
for contributions to Group III-V microwave power devices

Joy Laskar, Georgia Institute of Technology, Atlanta, GA, USA
for contributions to the modeling and development of high frequency communication modules

Kartikeya Mayaram, Oregon State Univ, Corvallis, OR, USA
for contributions to coupled device and circuit simulation

Deirdre R. Meldrum, University of Washington, Seattle, Washington, USA
for contributions to genome automation

John Melngailis, University of Maryland, College Park, MD, USA
for contributions to focused ion beam applications

Hisayo Sasaki Momose, Toshiba Corporation, Kanagawa, Japan
for contributions to ultra-thin gate oxide metal oxide semiconductor fields effect transistors

Mehrdad M. Moslehi, Semizone Inc., Palo Alto, CA, USA
for contributions to single wafer processing technologies

Laurence W. Nagel, Omega Enterprises, Randolph, NJ, USA
for contributions to the field of integrated circuit simulation

Hidehito Obayashi, Hitachi High-Technologies Corporation, Ibaraki, Japan
for contributions to critical dimension scanning electron microscopy

Yutaka Ohmori, Osaka University, Osaka, Japan
for contributions to the development of organic and semiconductor light emitting materials and devices

Shinji Okazaki, Assoc. of Super-Advanced Elec. Technologies, Tokyo, Japan
for contributions to the resolution enhancement technology in optical and electron-beam lithography

Manijeh Razeghi, Northwestern University, Evanston, IL, USA
for contributions to the development of compound semiconductor growth technology

Mark Stephen Rodder, Texas Instruments, Dallas, TX, USA
for contributions to deep sub-micron complementary metal oxide semiconductor technology

Enrico James Sangiorgi, University of Bologna, Cesna, Italy
for contributions to the modeling and characterization of hot carriers and non stationary transport effects in small silicon devices

Phillip Miles Smith, BAE Systems, Nashua, NH, USA
for contributions to microwave high electron mobility transistors

Tangali S. Sudarshan, Univ. of South Carolina, Columbia, SC, USA
for contributions to surface flashover of dielectric and semiconductor materials

Hidehiko Tanaka, University of Tokyo, Tokyo, Japan
for contributions to high performance computation models

Juzer M. Vasi, Indian Institute of Technology (IIT) Bombay, Mumbai, India
for leadership in microelectronics education

Sophie V. Verdonckt-Vandebroek, Xerox Corporation, Webster, NY, USA
for leadership in developing photocopier products

Lois D. Walsh, Air Force Research Lab, Rome, NY, USA
for leadership in electronic device reliability

Kevin John Webb, Purdue University, West Lafayette, IN, USA
for contributions to numerical modeling and characterization techniques of passive and active devices

Jason Chik-Shun Woo, UCLA, Los Angeles, CA, USA
for contributions to nanoscale silicon on insulator and bulk metal oxide semiconductor device physics and technology

**Donald Coolidge Wunsch, University of Missouri - Rolla, Rolla, MO,
USA**

*for contributions to hardware implementations of reinforcement and
unsupervised learning*

Kazuo Yano, Central Research Laboratory, Hitachi, Ltd., Tokyo, Japan

*for contributions to nanostructured-silicon devices and circuits and
advanced CMOS logic*